

WHAT IS CLAIMED IS:

1. A method for fabricating an image sensor, the method comprising:

forming an over coat layer on an upper face of a semiconductor substrate on which a color filter layer is formed;

forming a microlens on the over coat layer;

covering the microlens with a protection layer;

back grinding a lower face of the semiconductor substrate; and

removing the protection layer of the microlens.
2. The method for fabricating the image sensor as claimed in claim 1, wherein the protection layer of the microlens is formed of Spin On Glass (SOG).
3. The method for fabricating the image sensor as claimed in claim 2, wherein the method further comprises curing the protection layer.
4. The method for fabricating the image sensor as claimed in claim 3, wherein a curing temperature of the curing is in a range of 150 to 300°C.

5. The method for fabricating the image sensor as claimed in claim 3, wherein a curing time of the curing is around 30 minutes.

6. The method for fabricating the image sensor as claimed in claim 1, wherein the removing comprises applying one of buffered HF (BHF) and dilute HF (DHF) onto the protection layer.